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PATENTS/APPLICATIONS:

1. US#5066615 – **PHOTOLITHOGRAPHIC PROCESSES USING THIN COATINGS OF REFRACTORY METAL SILICON NITRIDES AS ANTIREFLECTION LAYERS.** M.F. Brady, J.K. Dorey, and A.L. Helms, Jr., Issued November 19, 1991.

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5. US#20050175789 – **METHOD FOR ENERGY-ASSISTED ATOMIC LAYER DEPOSITION AND REMOVAL.** Aubrey L. Helms, Jr., Kerem Kapkin, Sang-In Lee, and Yoshihide Senzaki, Utility Application filed June 23, 2003.

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7. Application filed in general area of ALD Precursors**.** Aubrey L. Helms, Jr., and Yoshi Senzaki, Provisional Application filed March 1, 2004. [Dropped by Assignee-?]

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